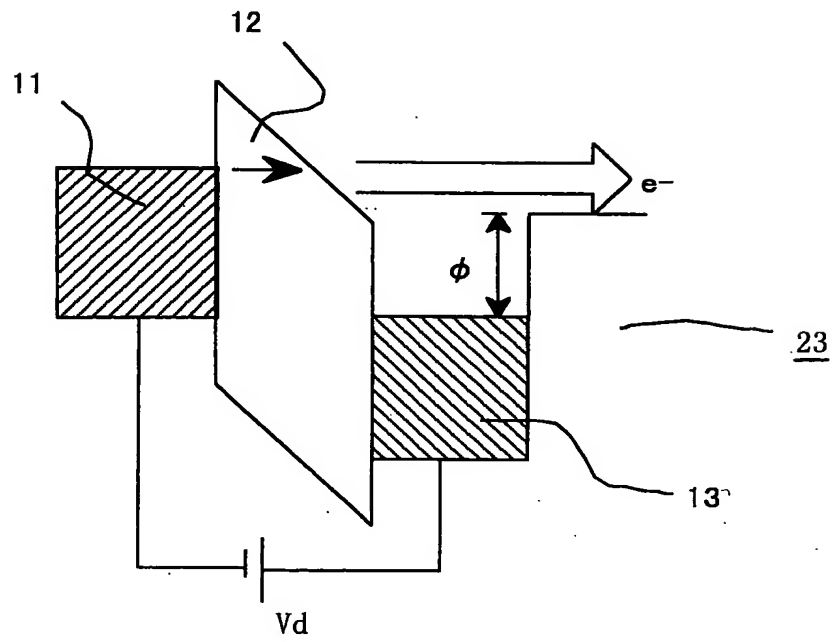


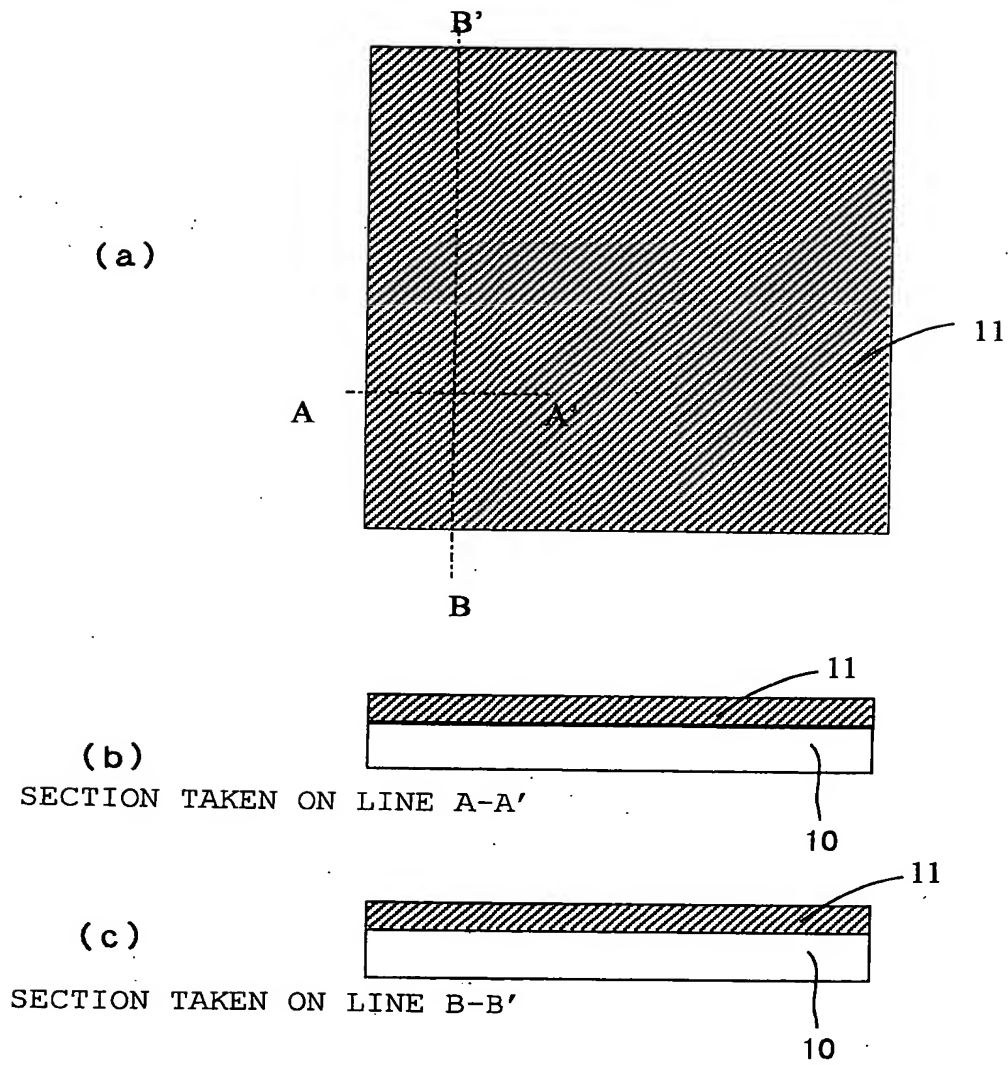
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FIG. 1



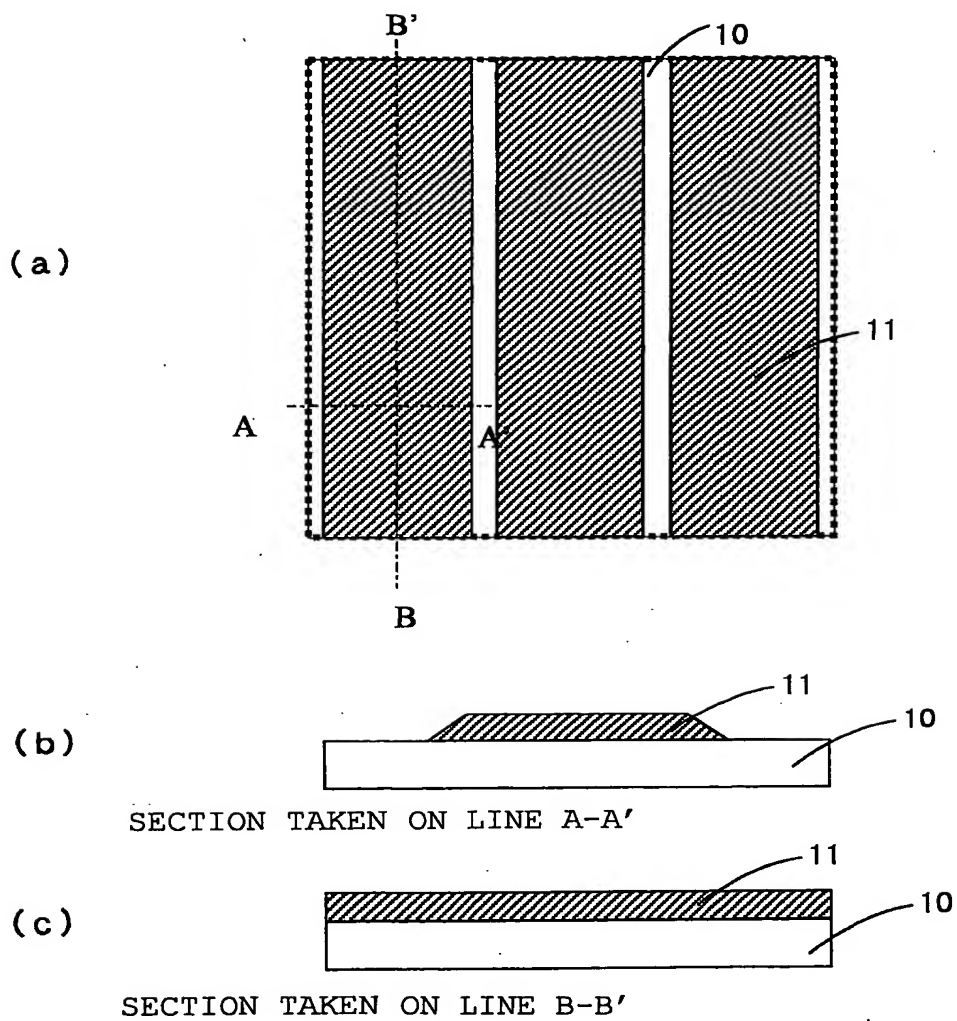
2/30

FIG.2



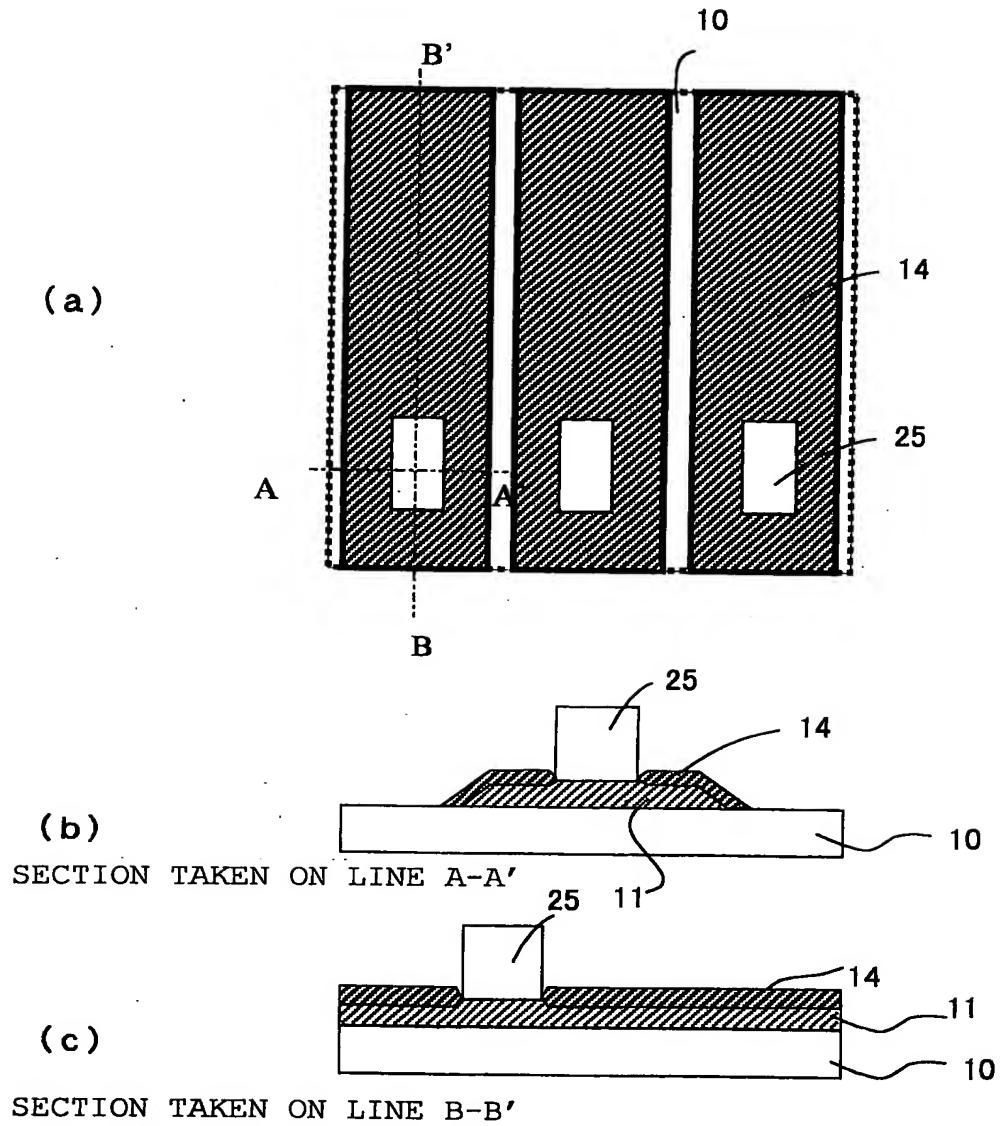
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FIG.3



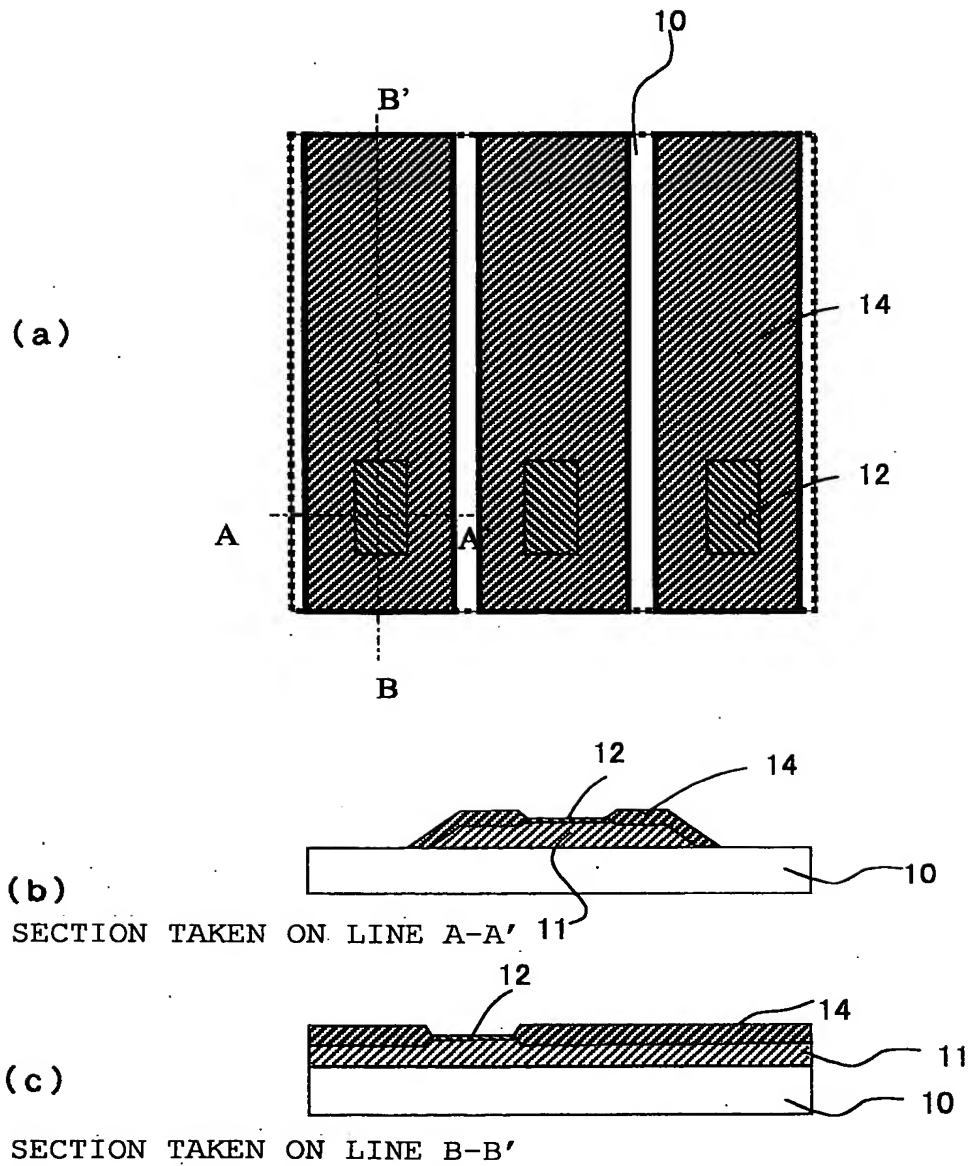
4/30

FIG.4



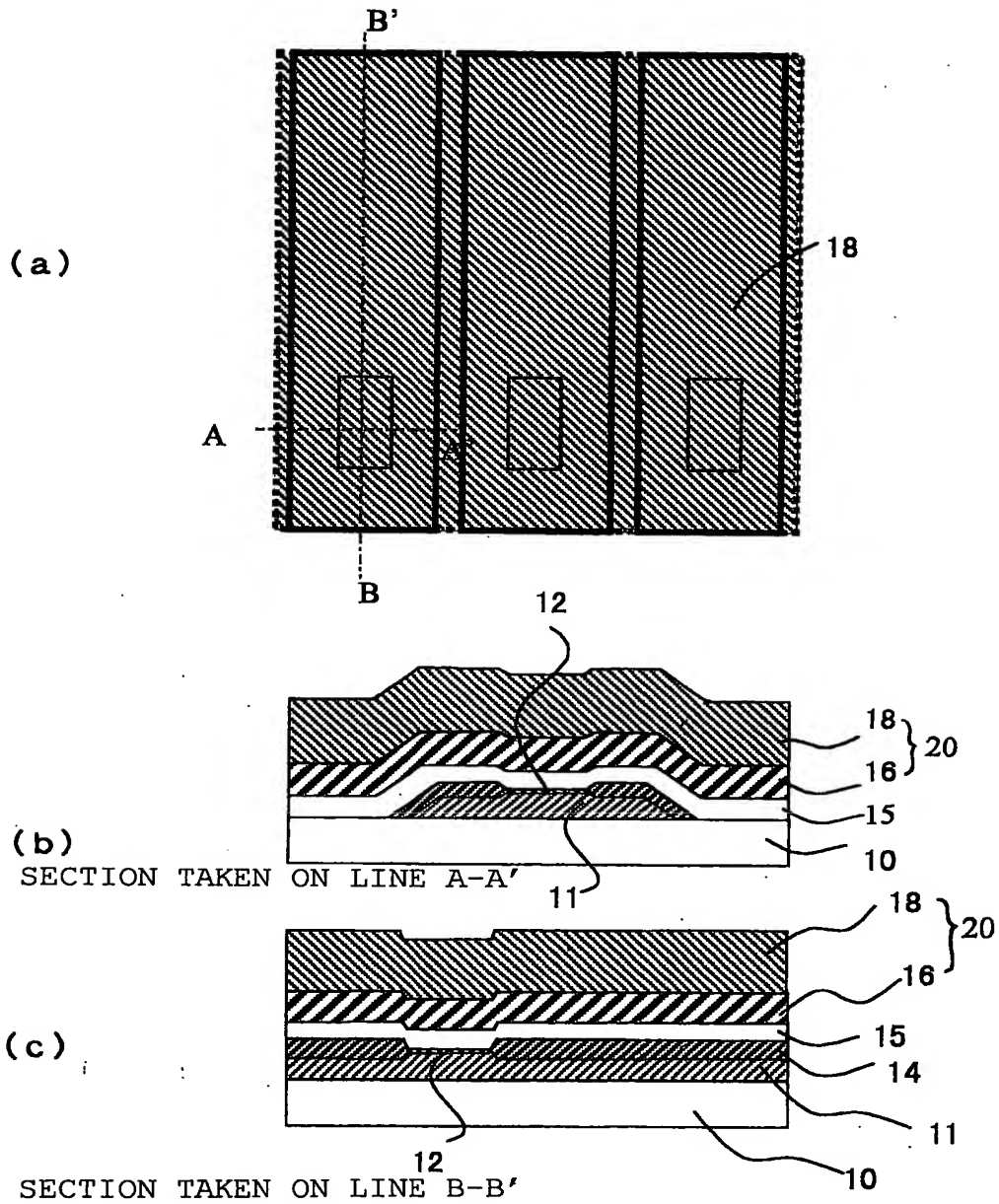
5/30

FIG.5



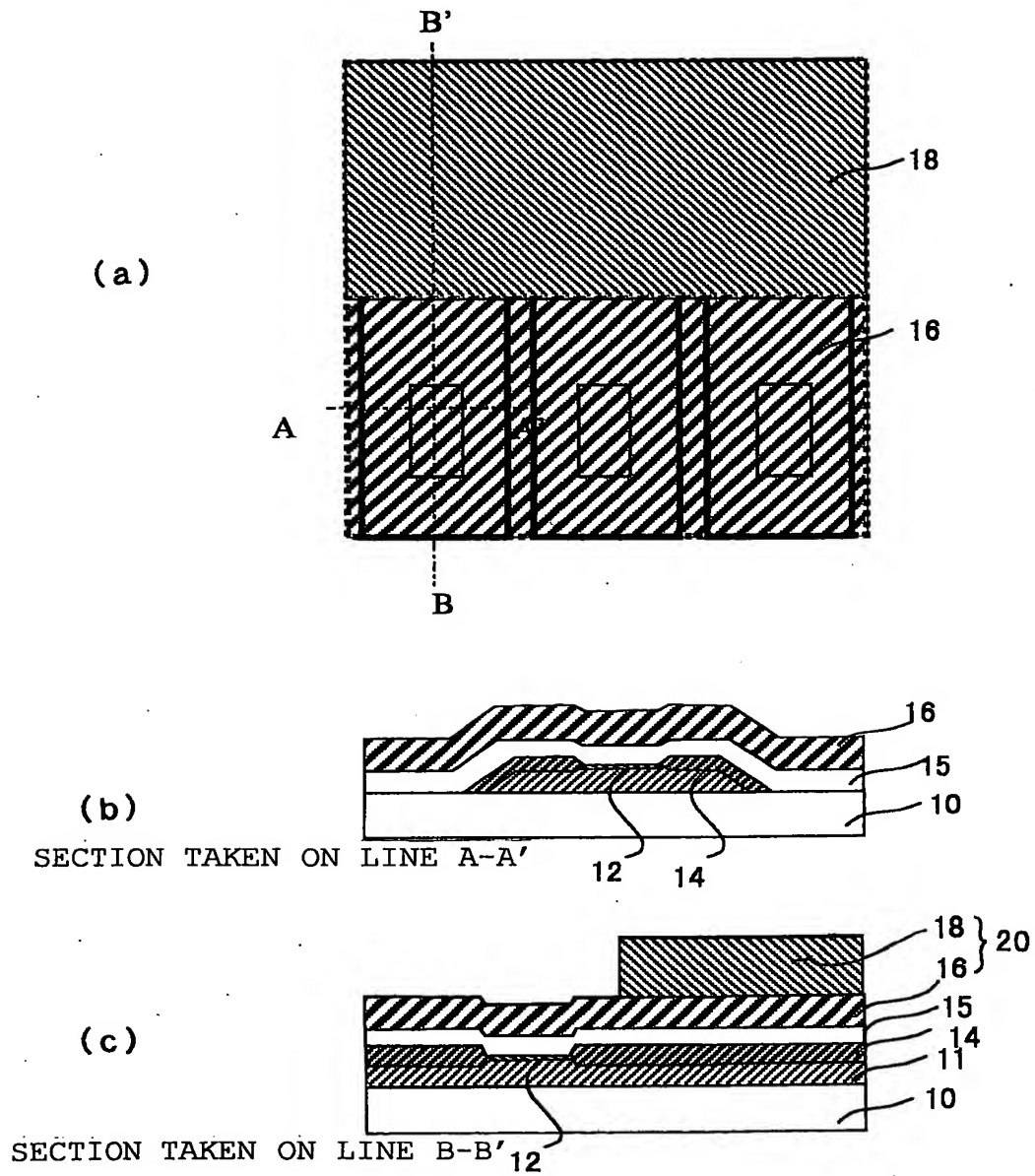
6/30

FIG. 6



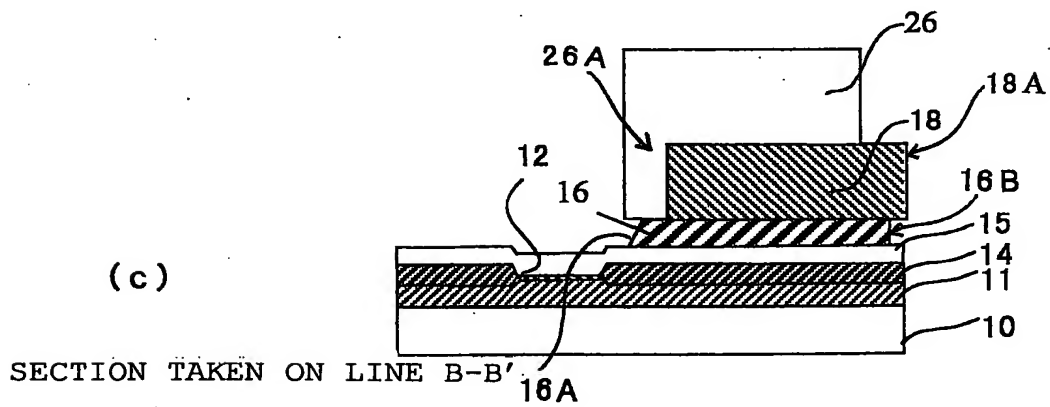
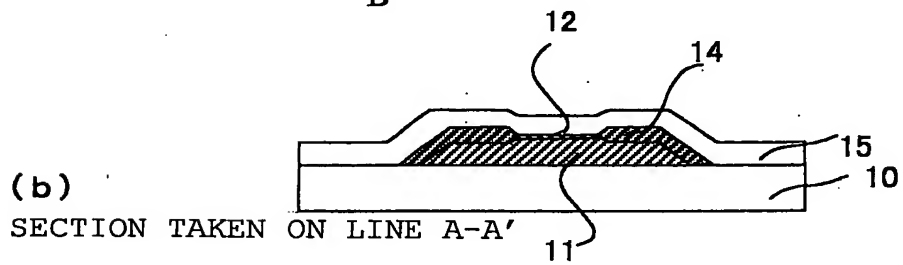
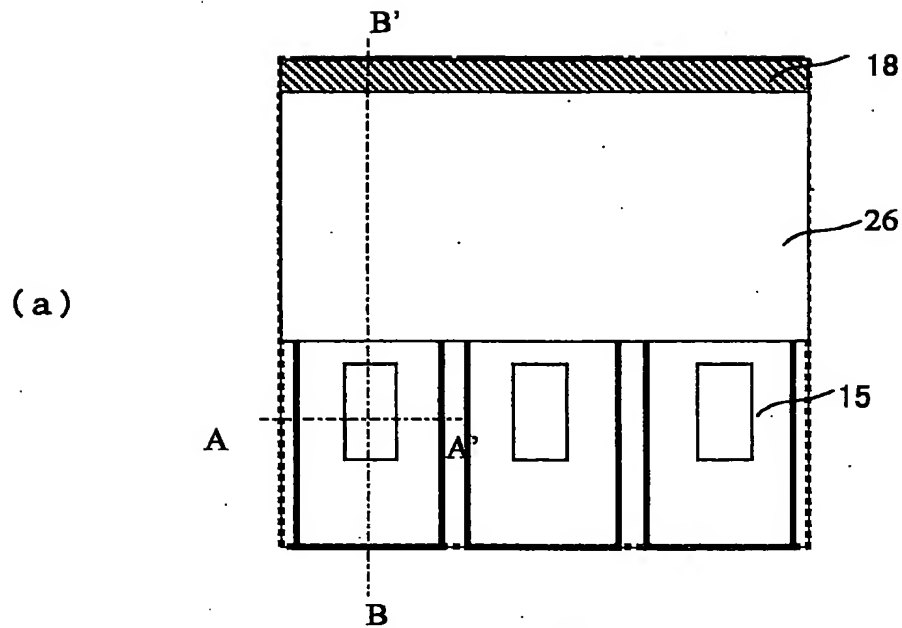
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FIG. 7



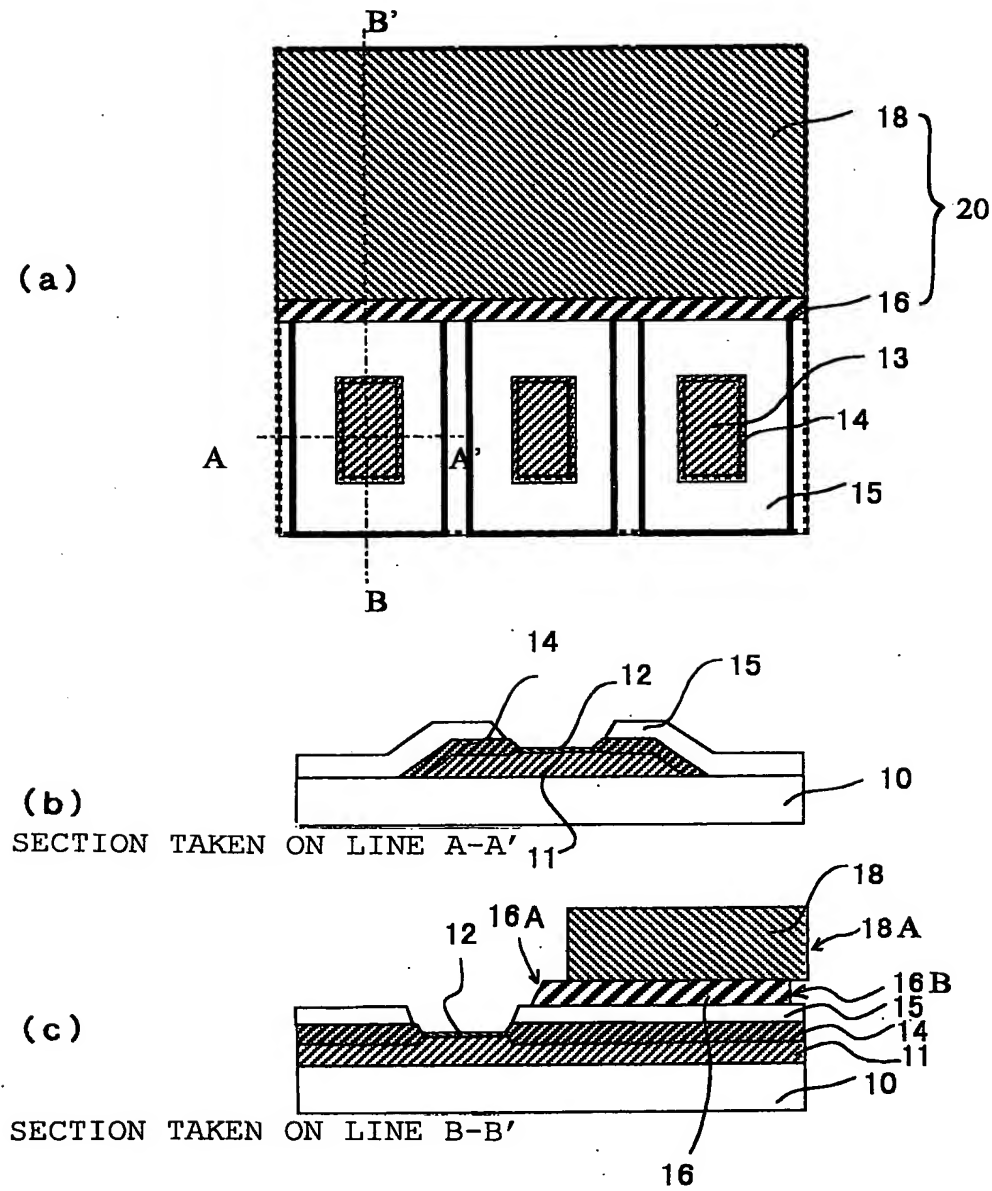
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FIG.8



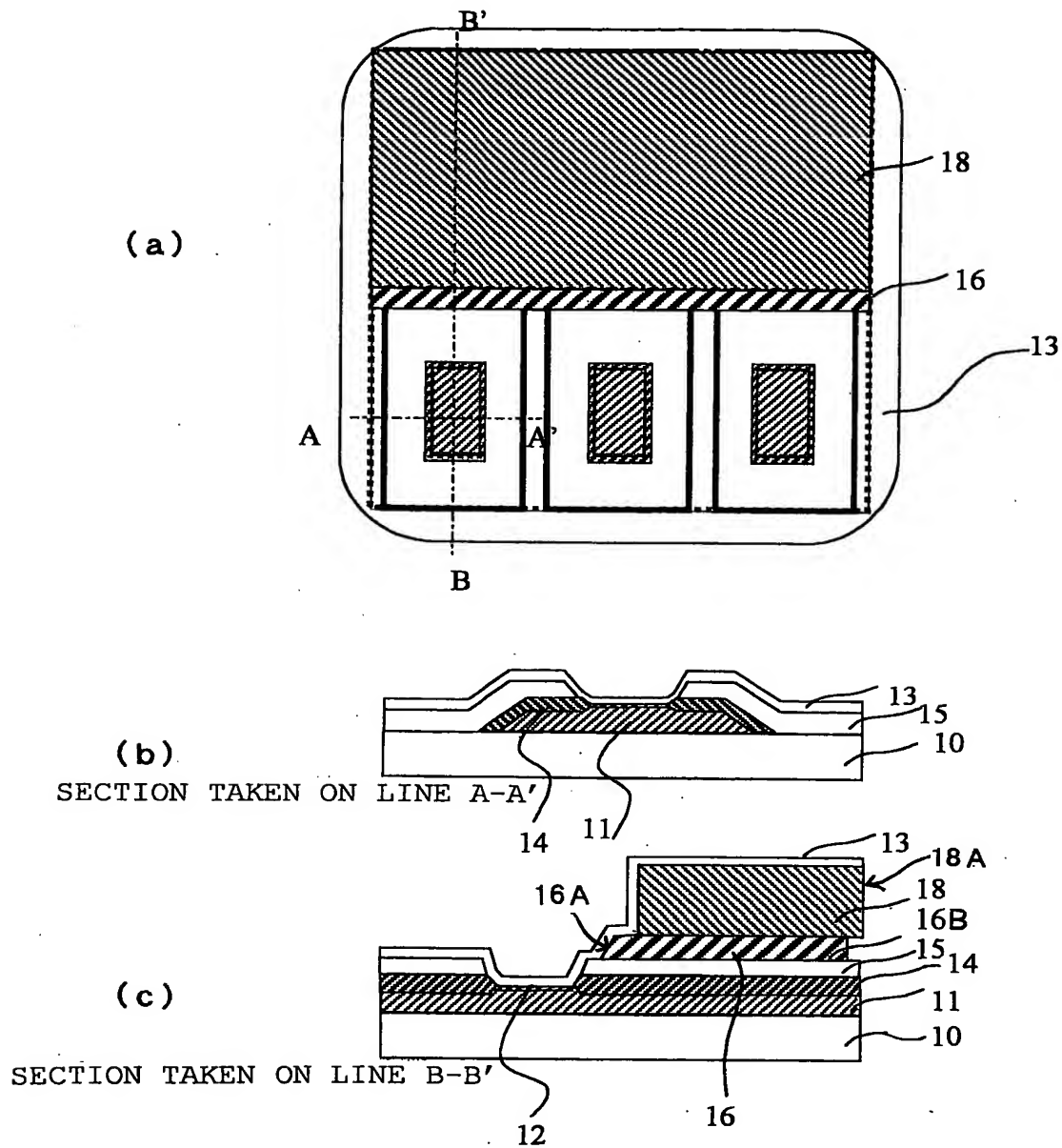
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FIG.9



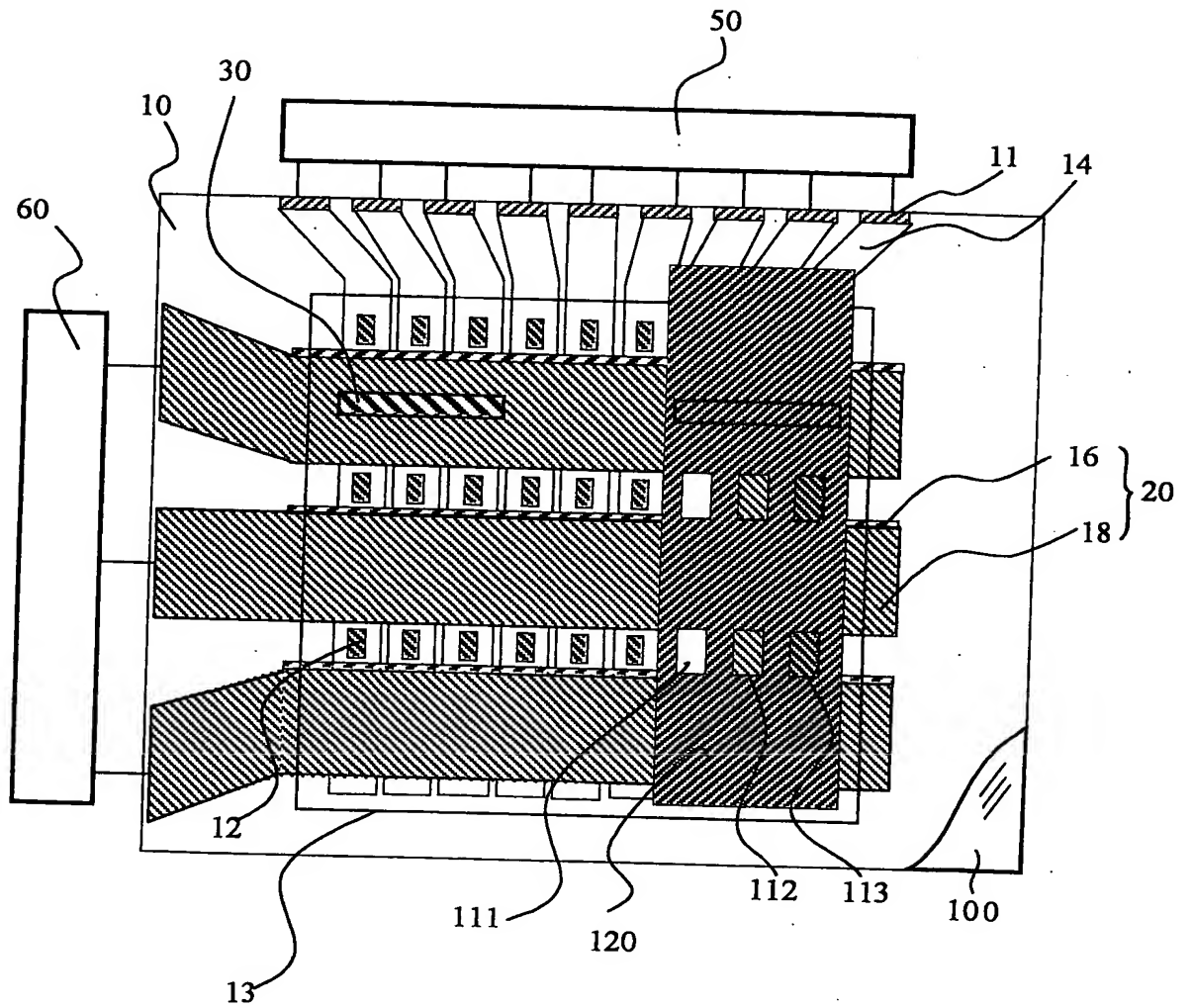
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FIG. 10



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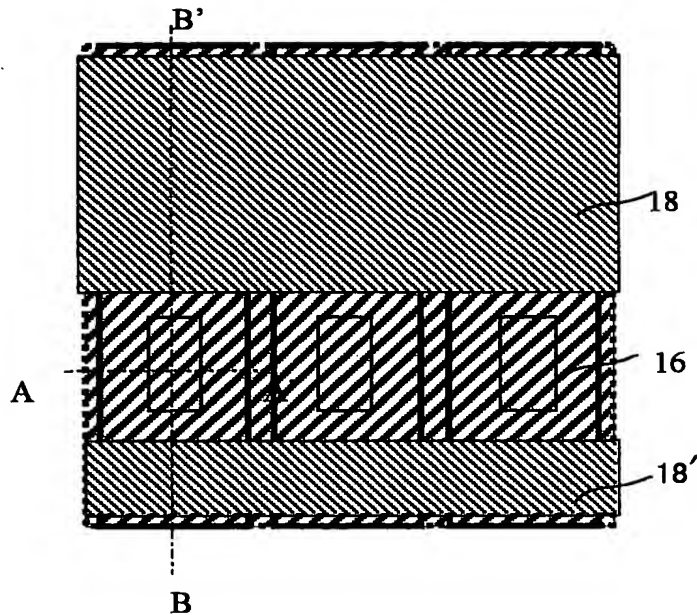
FIG. 11



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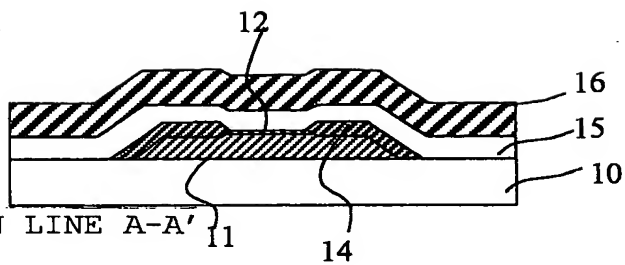
FIG.12

(a)



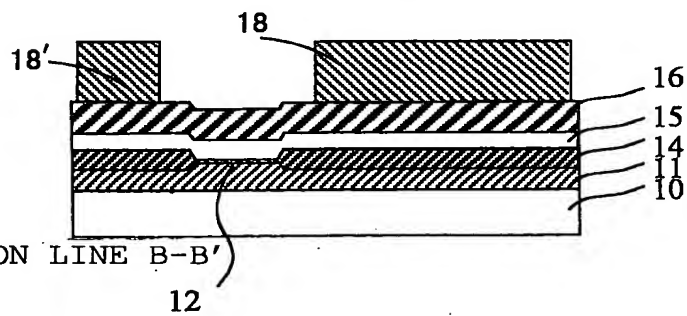
(b)

SECTION TAKEN ON LINE A-A'



(c)

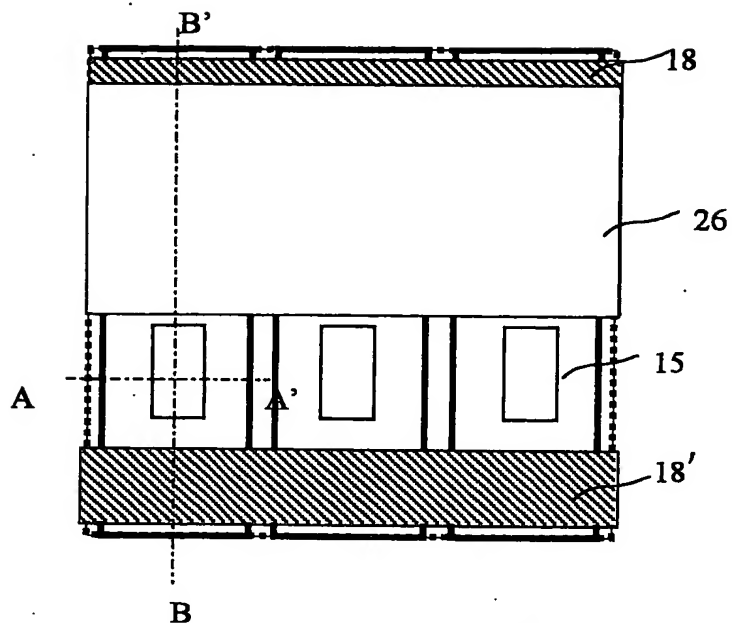
SECTION TAKEN ON LINE B-B'



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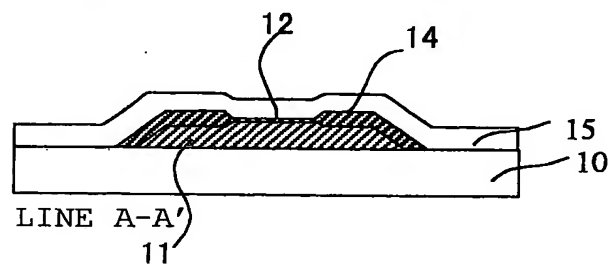
FIG.13

(a)



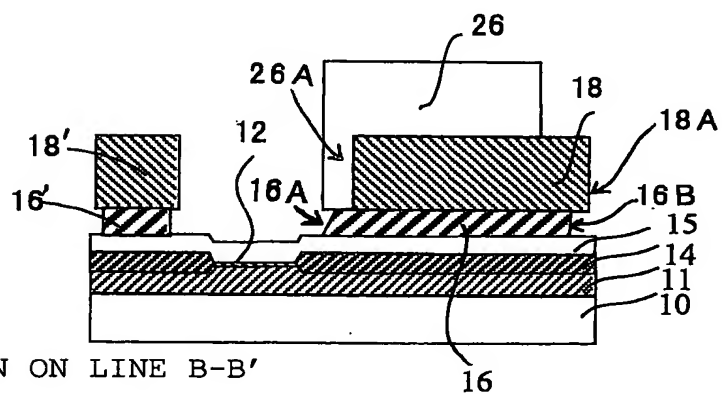
(b)

SECTION TAKEN ON LINE A-A'



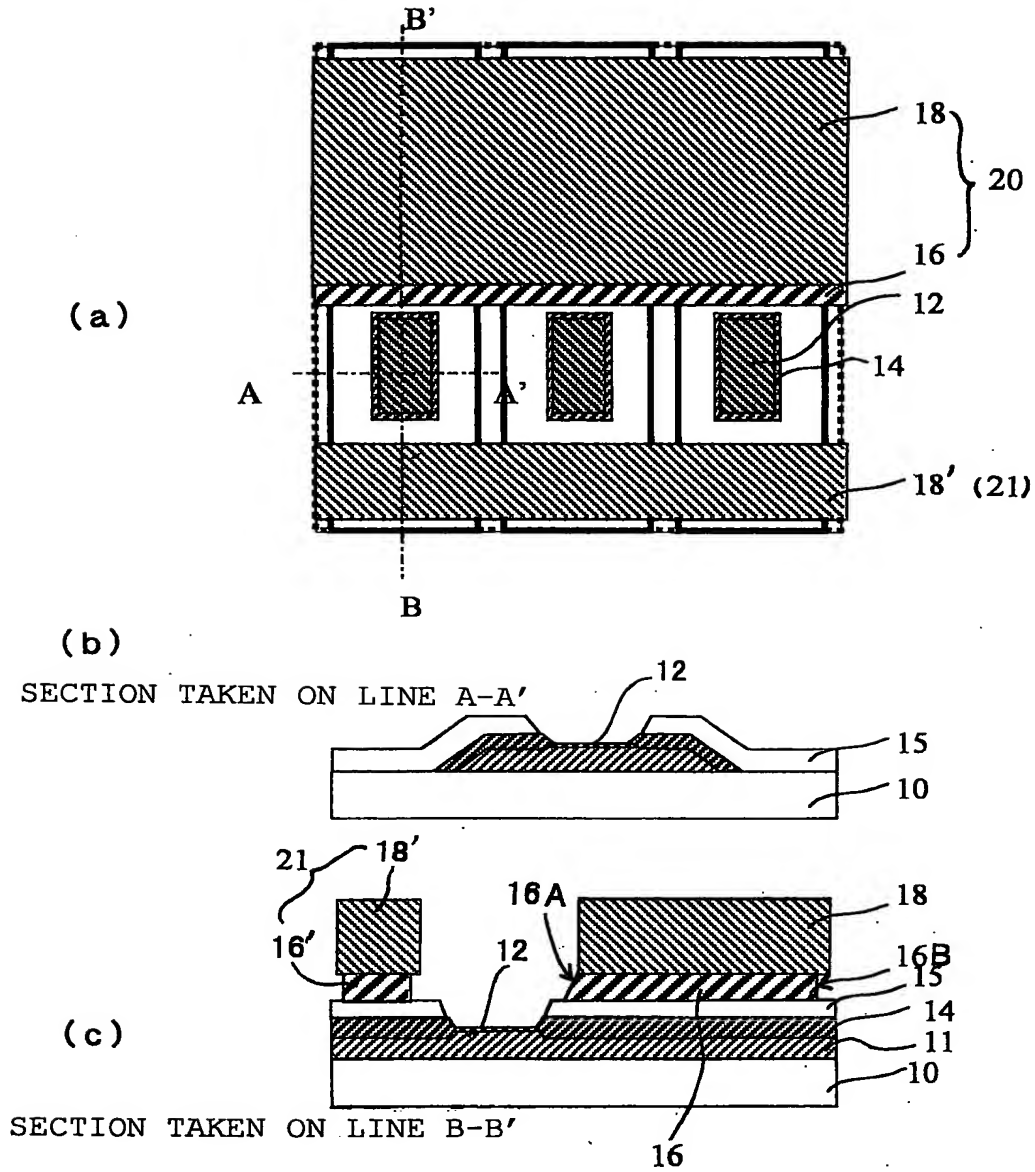
(c)

SECTION TAKEN ON LINE B-B'



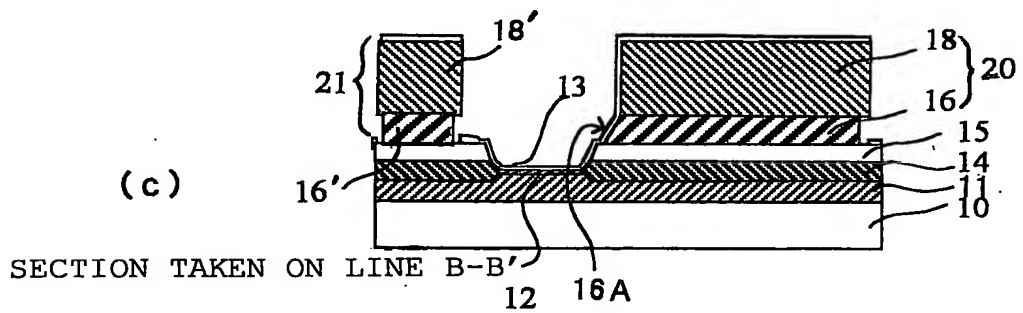
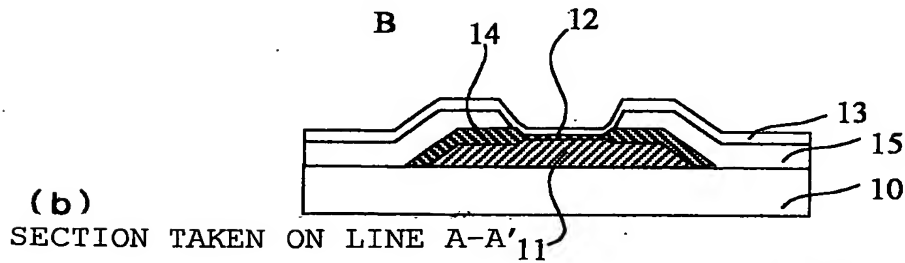
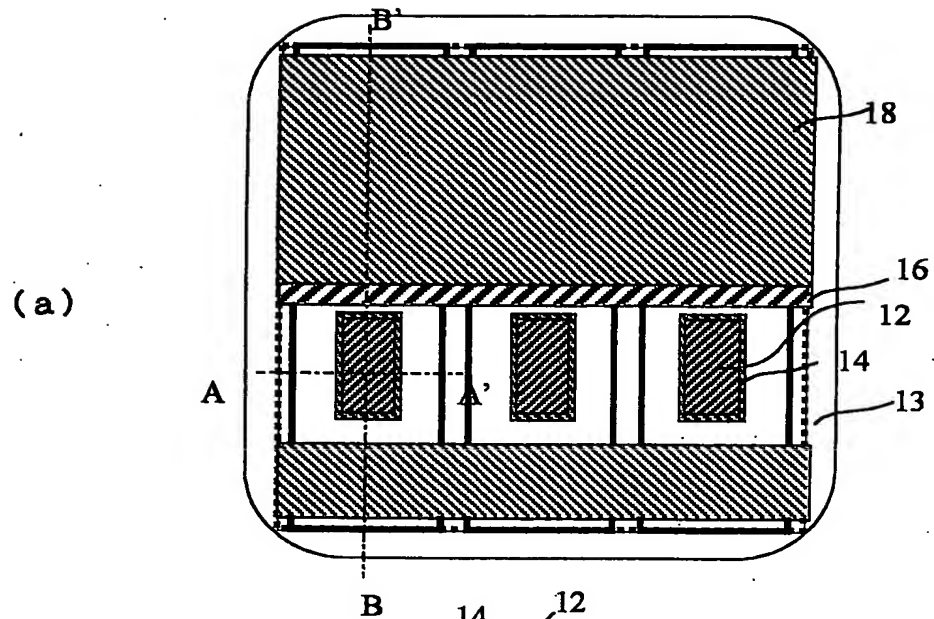
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FIG. 14



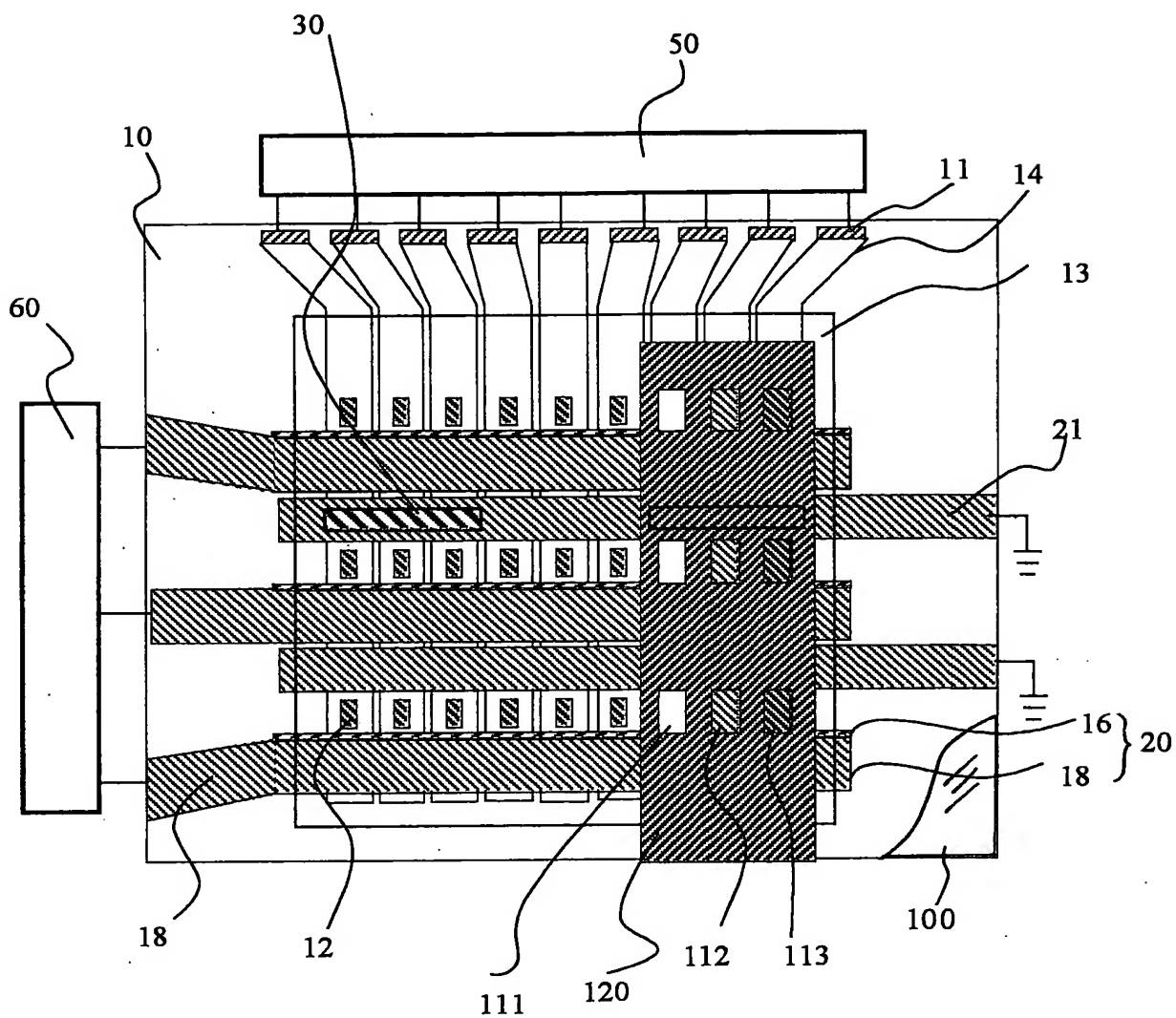
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FIG.15



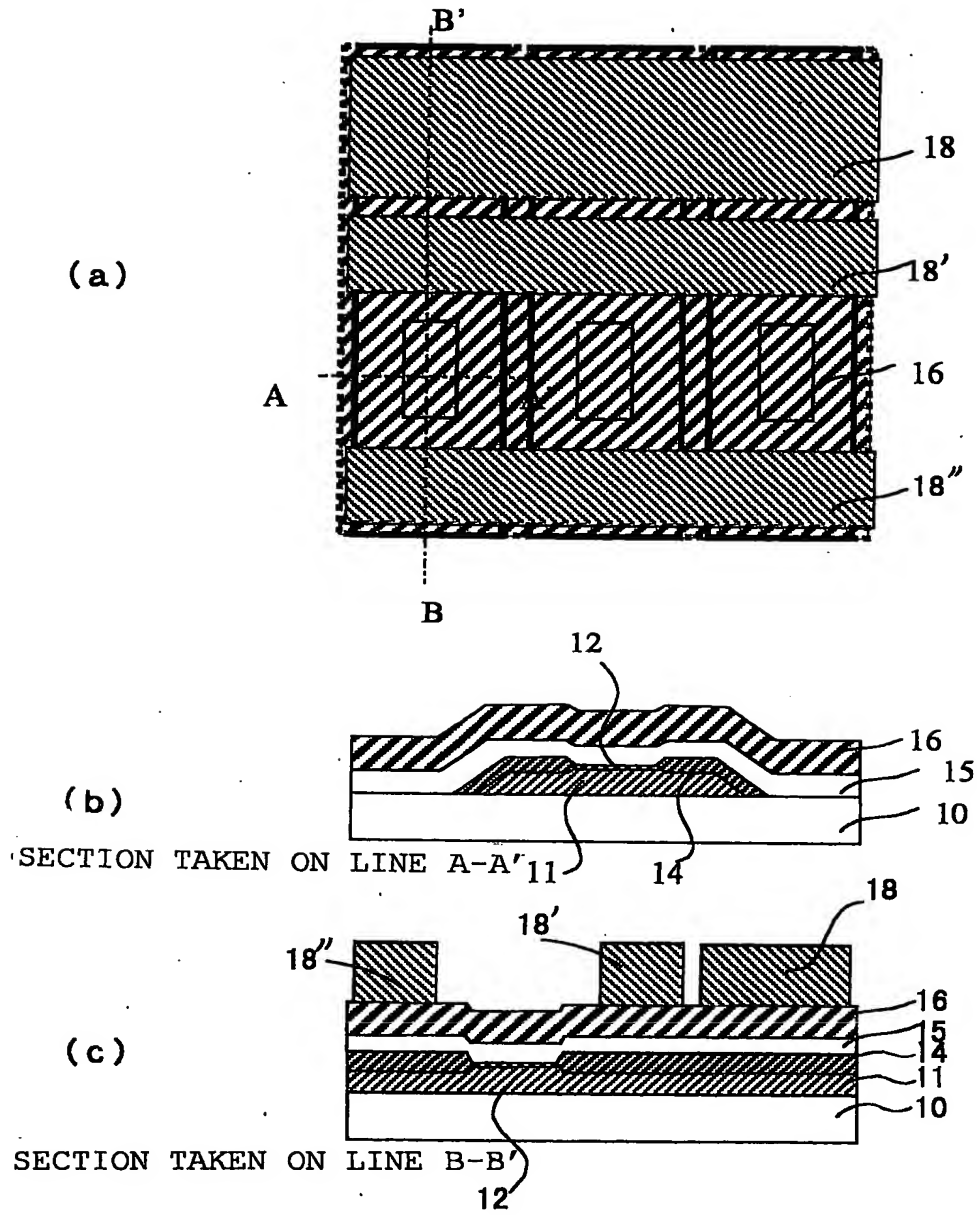
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FIG. 16



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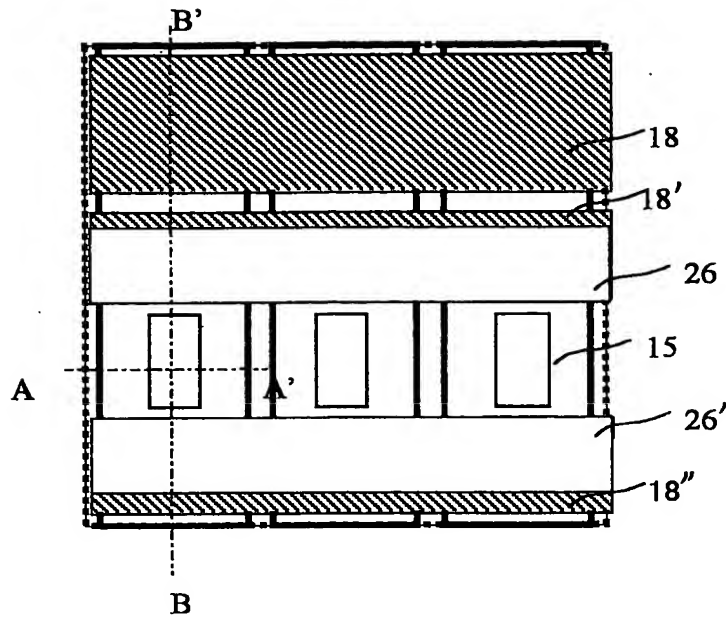
FIG.17



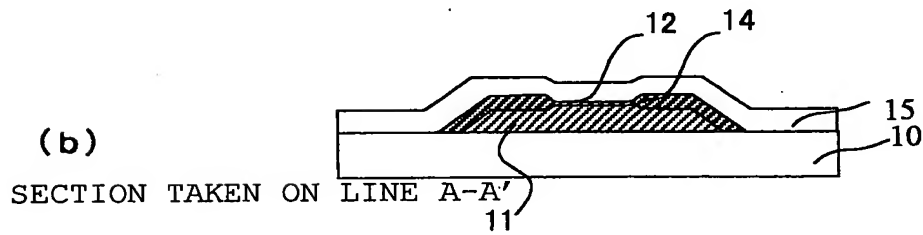
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FIG. 18

(a)

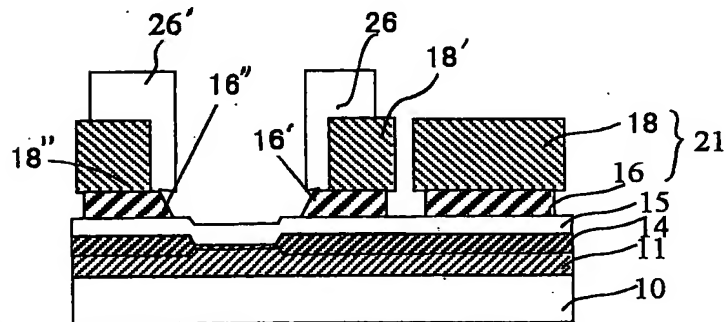


(b)



SECTION TAKEN ON LINE A-A'

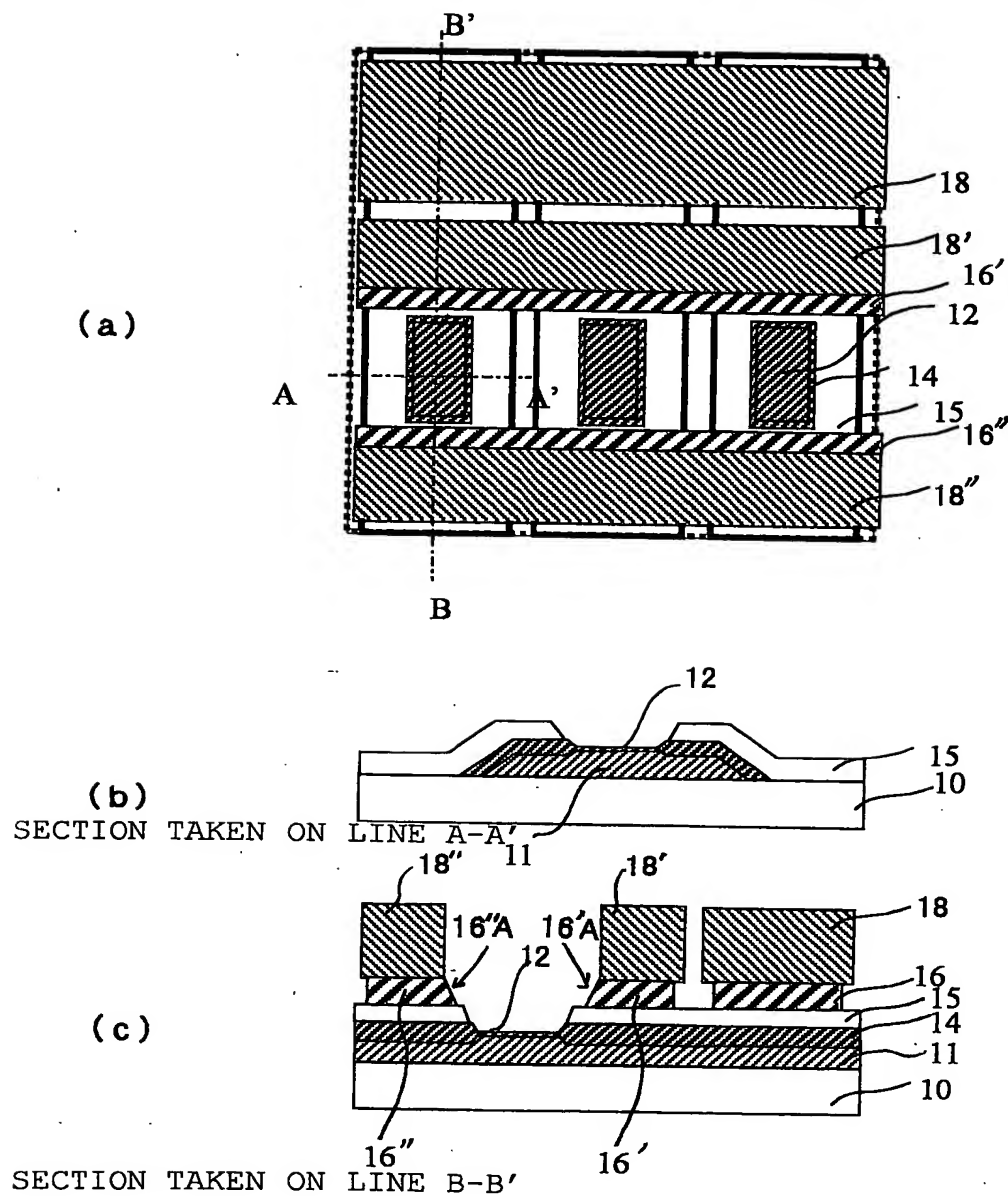
(c)



SECTION TAKEN ON LINE B-B'

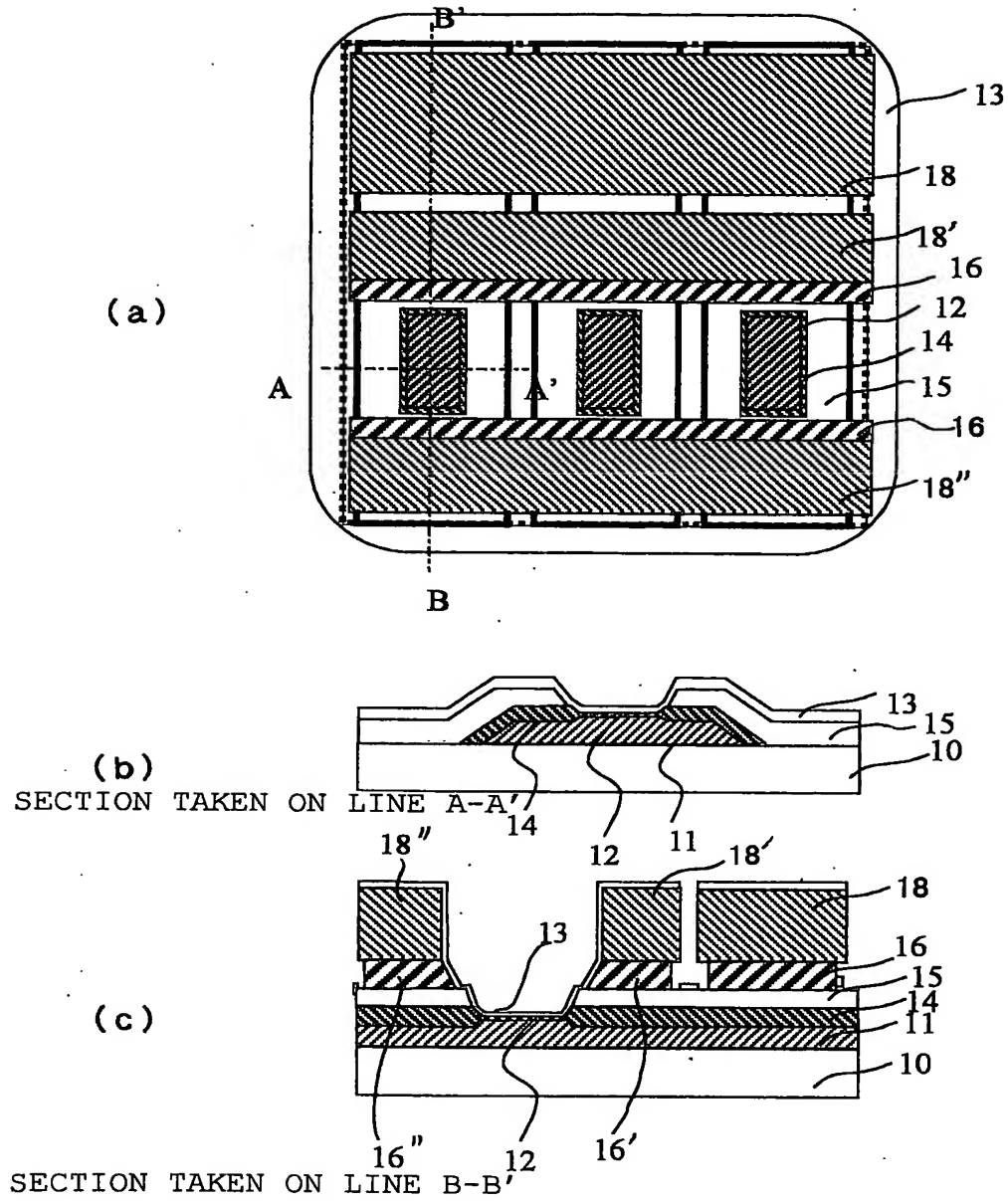
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FIG. 19



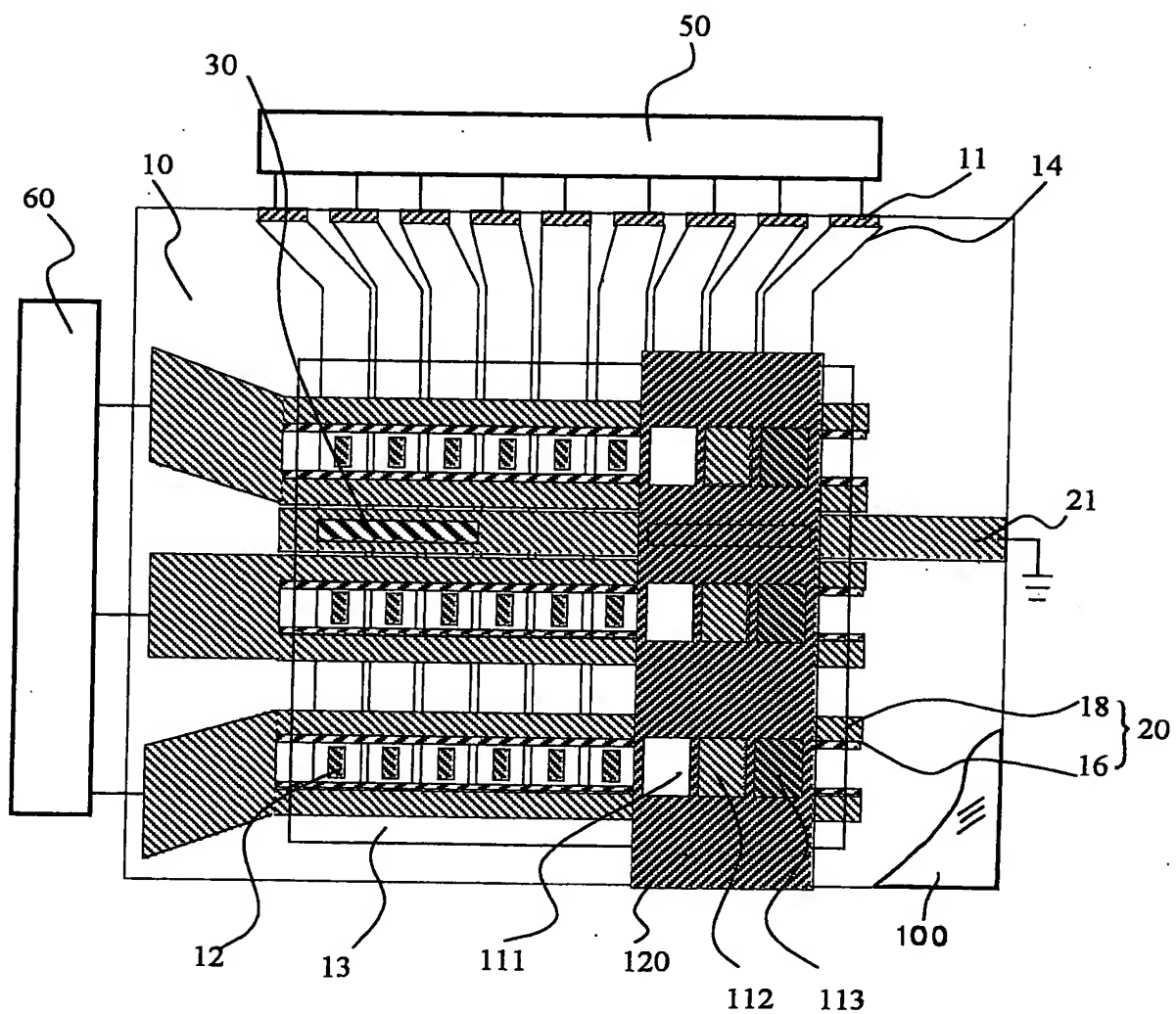
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FIG.20



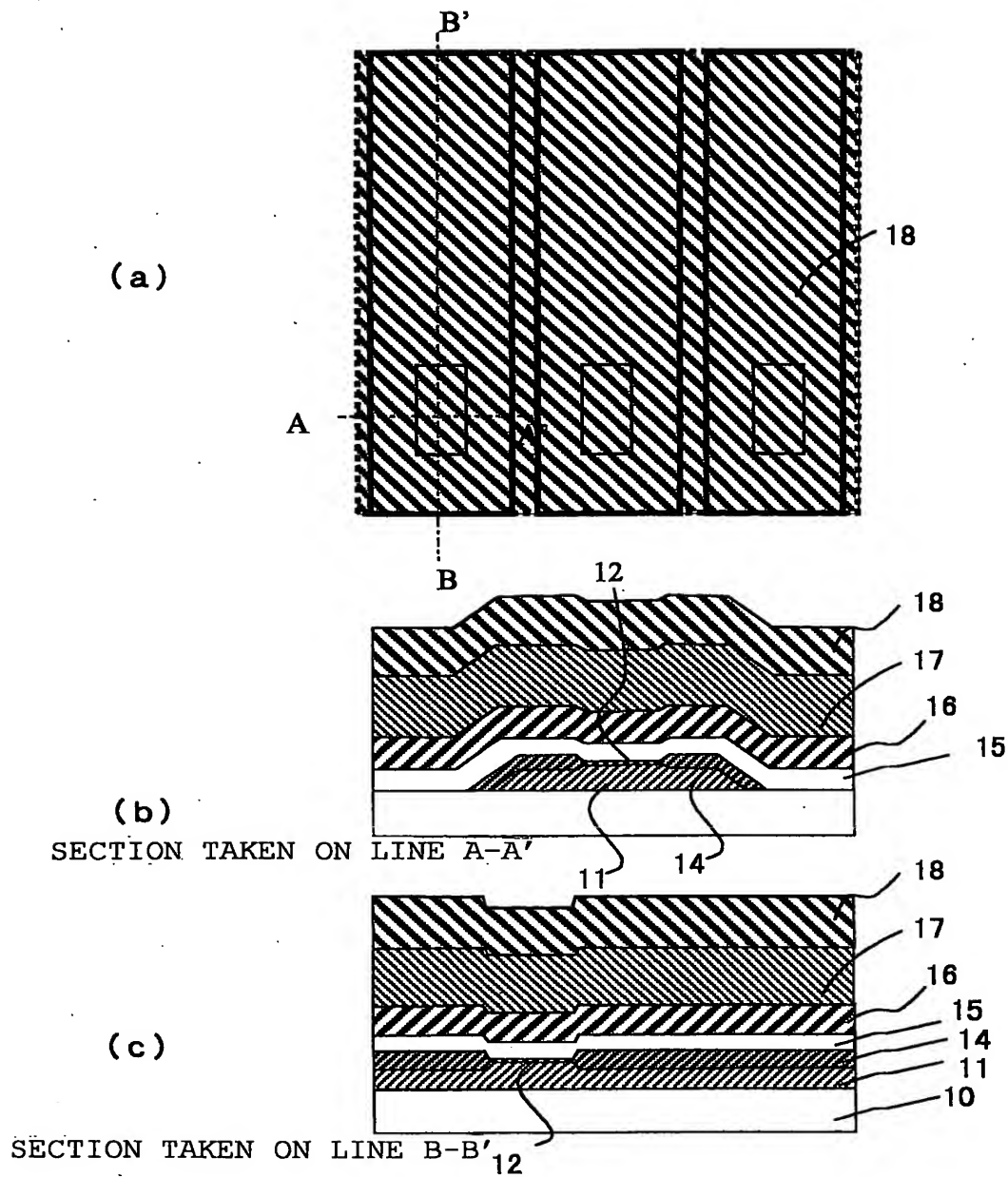
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FIG.21



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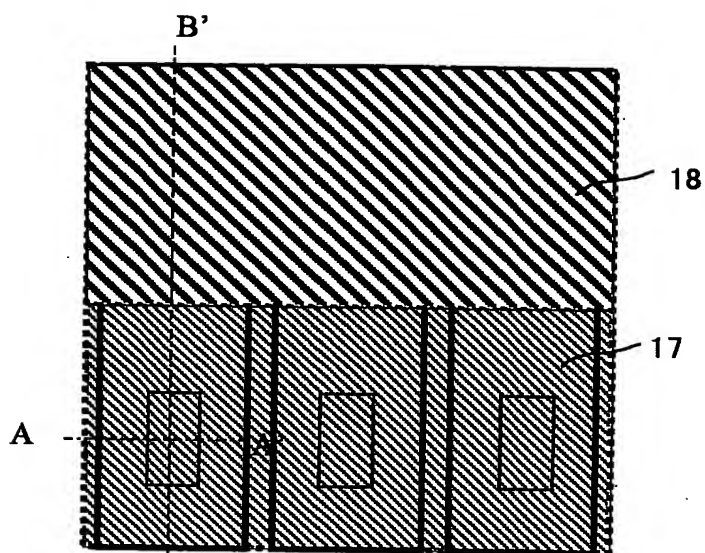
FIG.22



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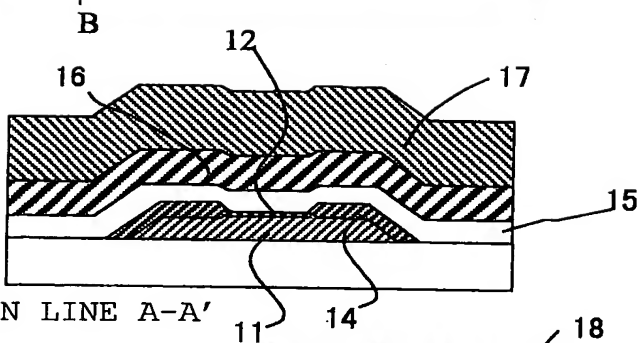
FIG.23

(a)



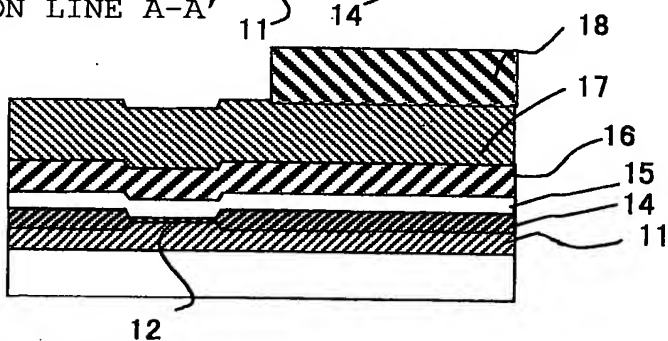
(b)

SECTION TAKEN ON LINE A-A'



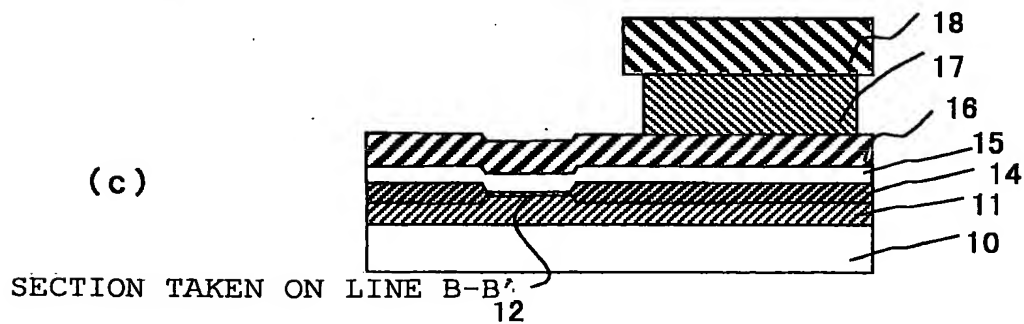
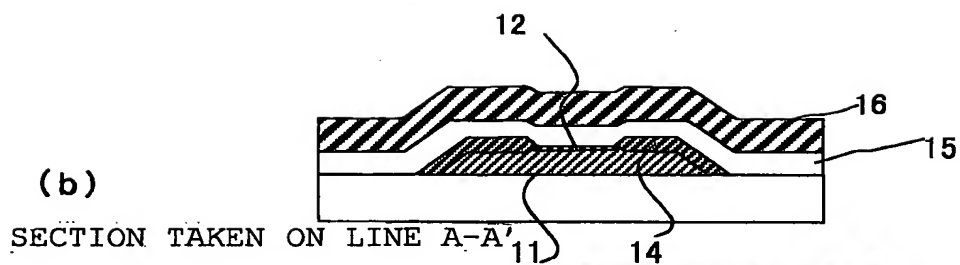
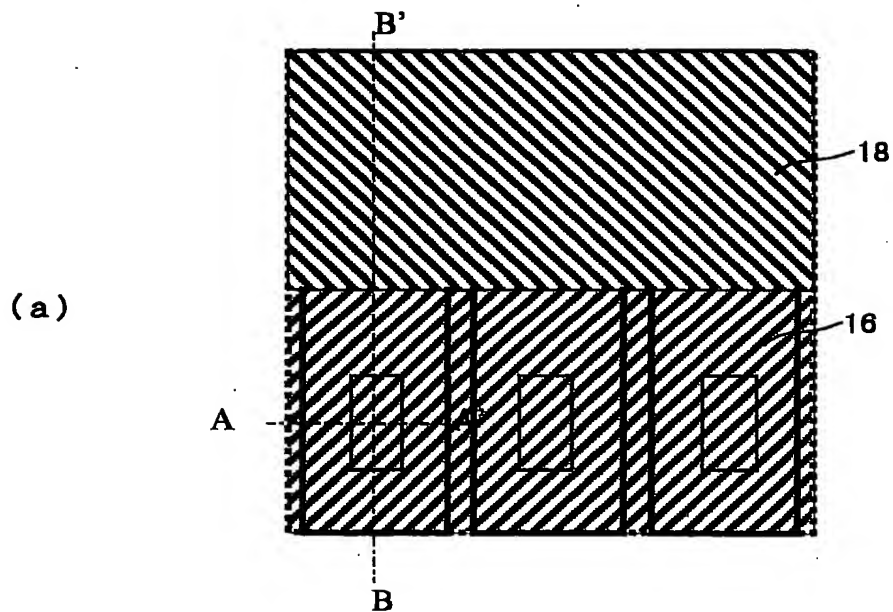
(c)

SECTION TAKEN ON LINE B-B'



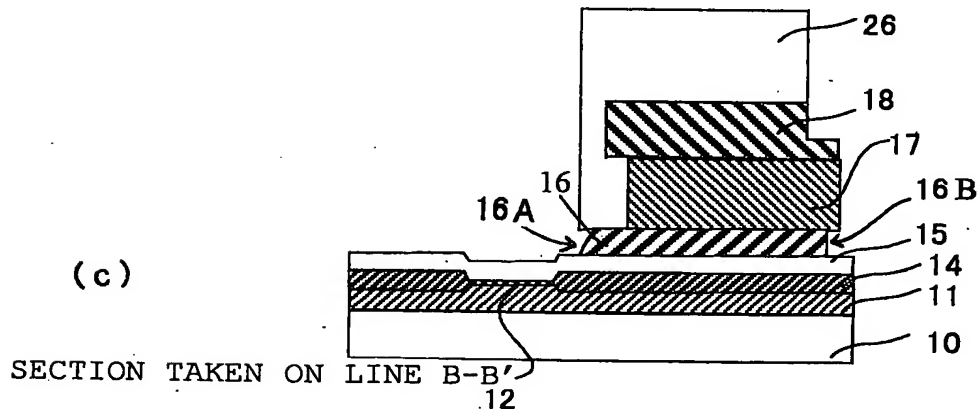
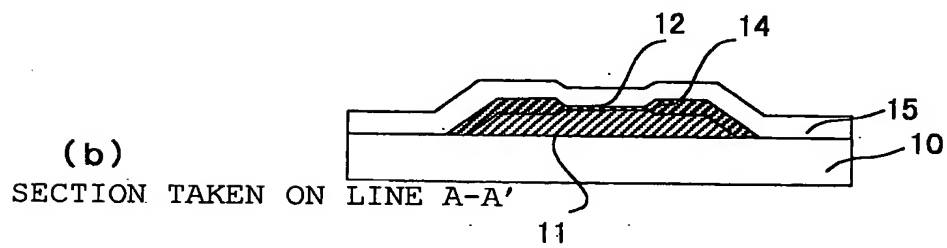
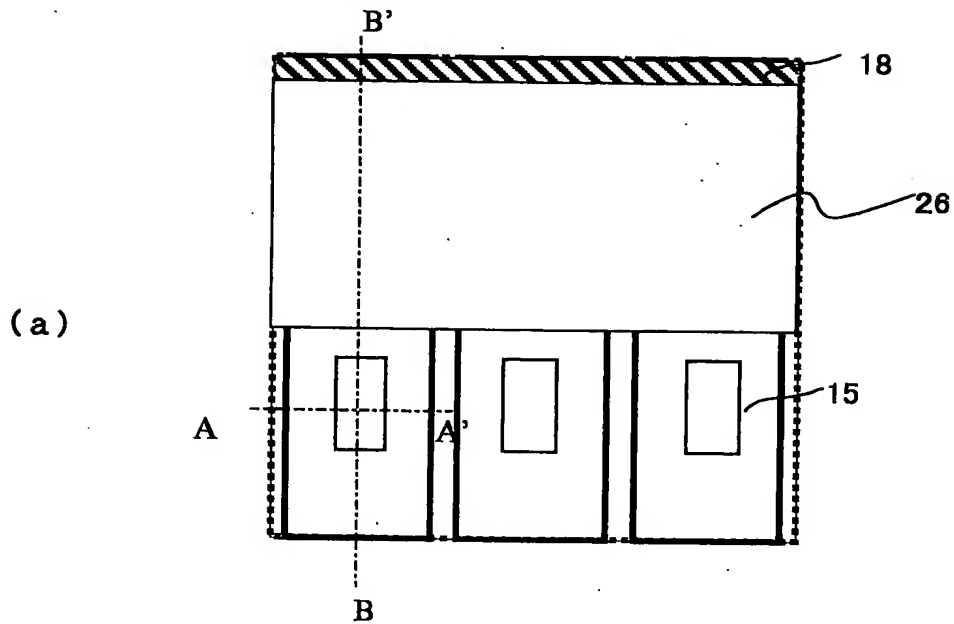
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FIG.24



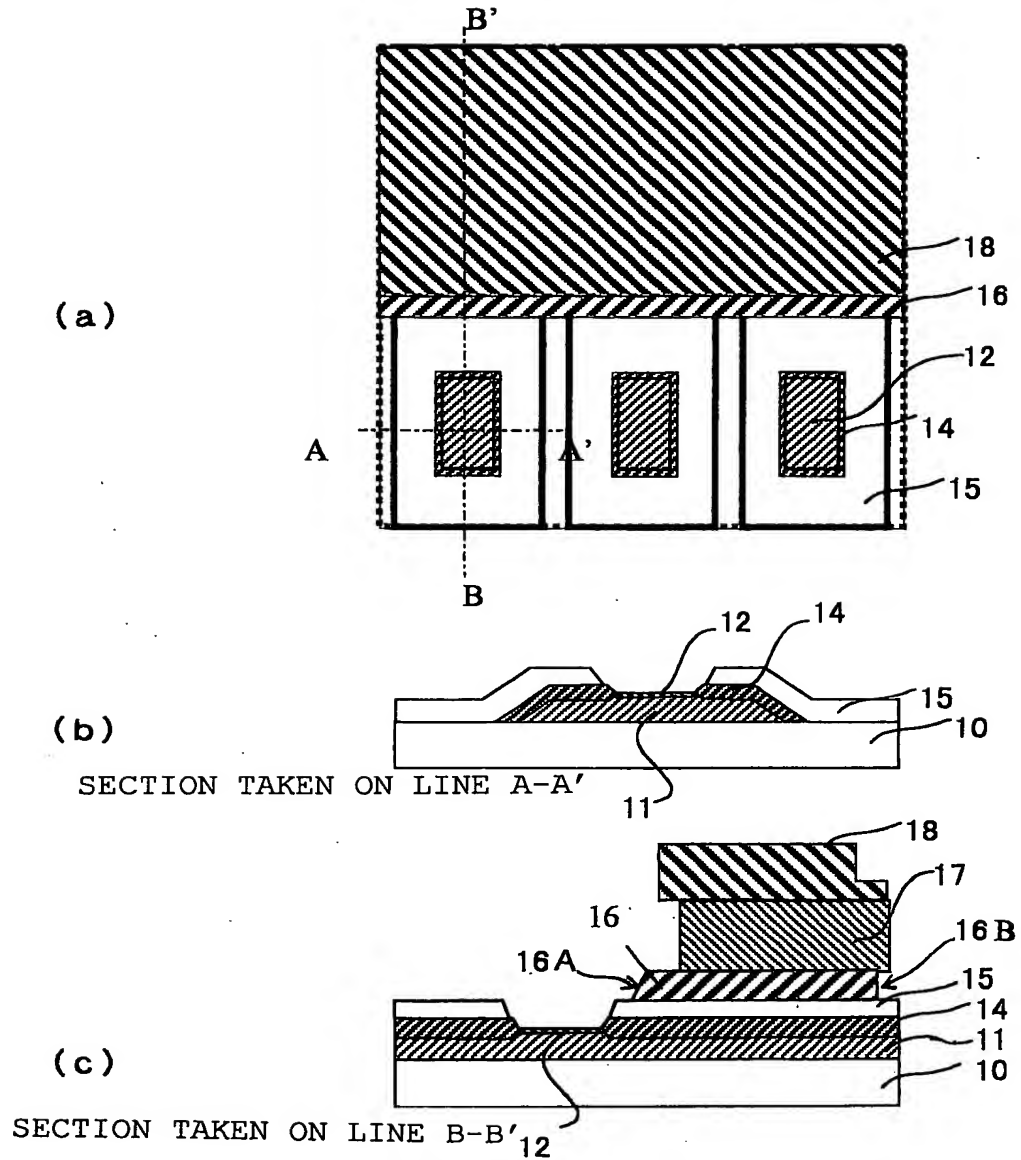
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FIG.25

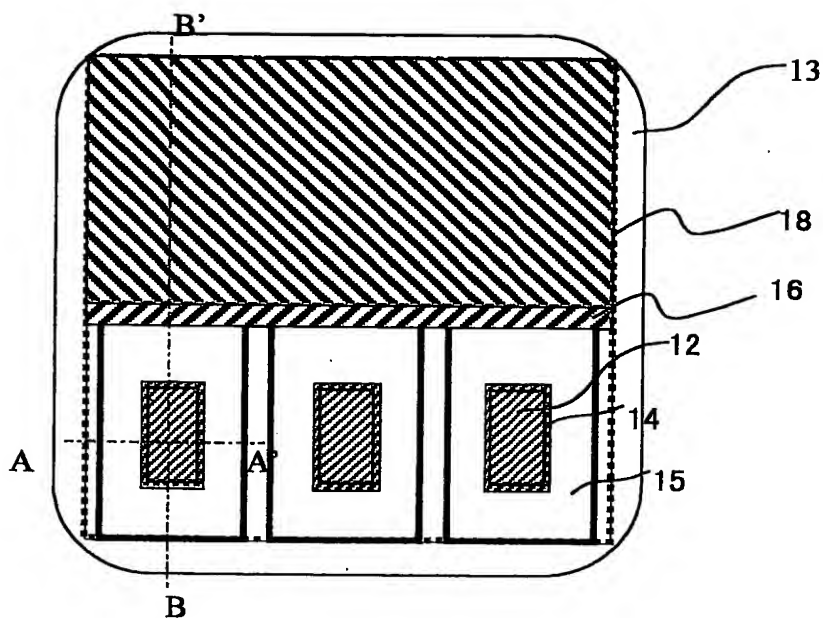


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FIG.26



(a)



(b)

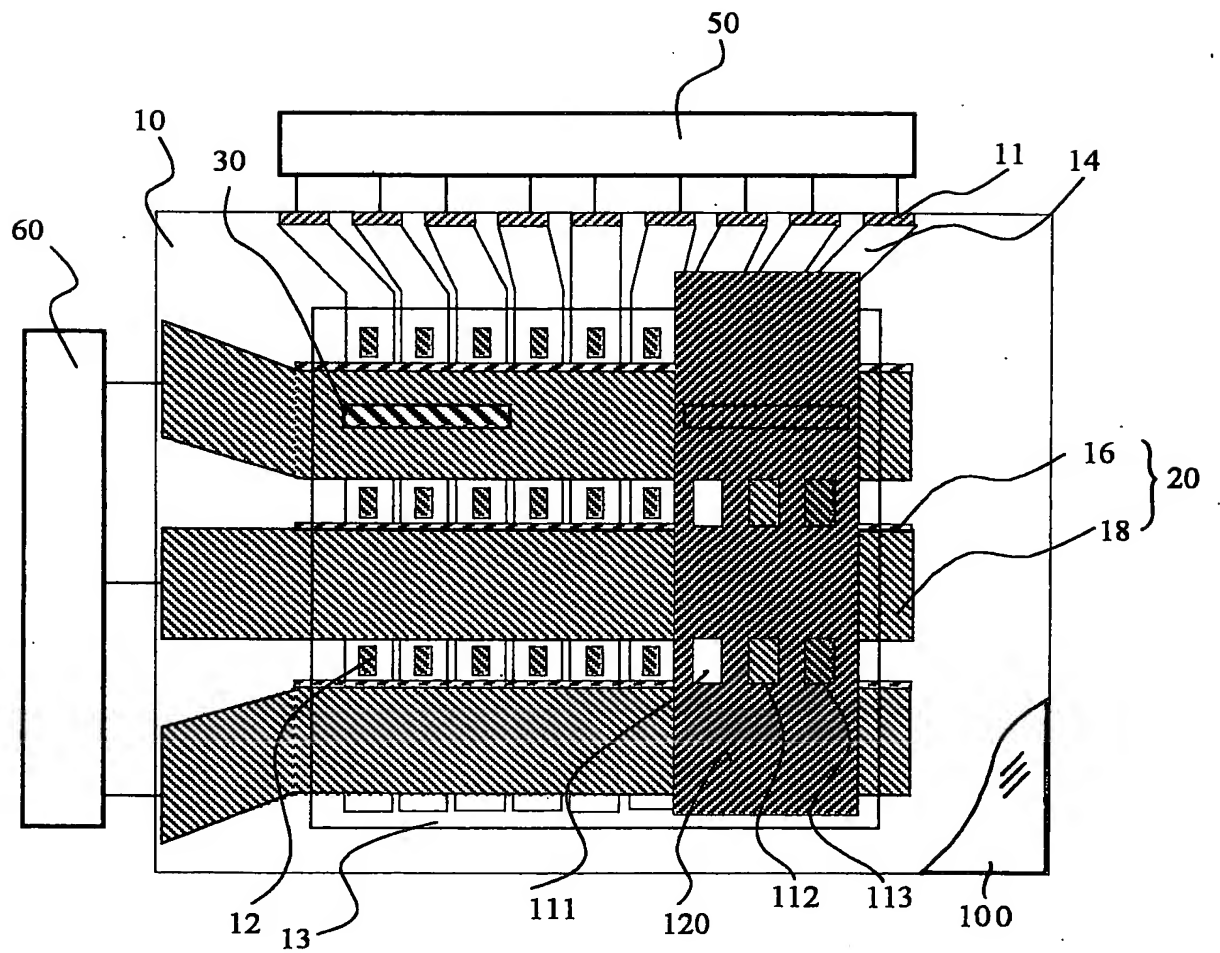
A cross-sectional view of a semiconductor device along line A-A'. The device consists of a substrate 10 with a thin layer 15 on its top surface. A central region 12 is filled with a material indicated by diagonal hatching. This central region is flanked by two side regions 11 and 14. Above the central region 12, there is a layer 13 that forms a raised, stepped structure. The label 'LINE A-A'' is positioned below the substrate 10, indicating the plane of the cross-section.

(c)

This cross-sectional view, taken along line B-B', shows the internal structure of the device. It features a substrate (10) with a base layer (11) and a patterned layer (12). Above this, there is a layer (13) with a central opening. A layer (14) is deposited over the opening, and a layer (15) is on top of it. A layer (16) is also present, with a portion labeled 16A. A layer (17) is on top of 16, and a layer (18) is the topmost layer. A layer (19) is also indicated. The diagram shows the relationship between these various layers and the central opening.

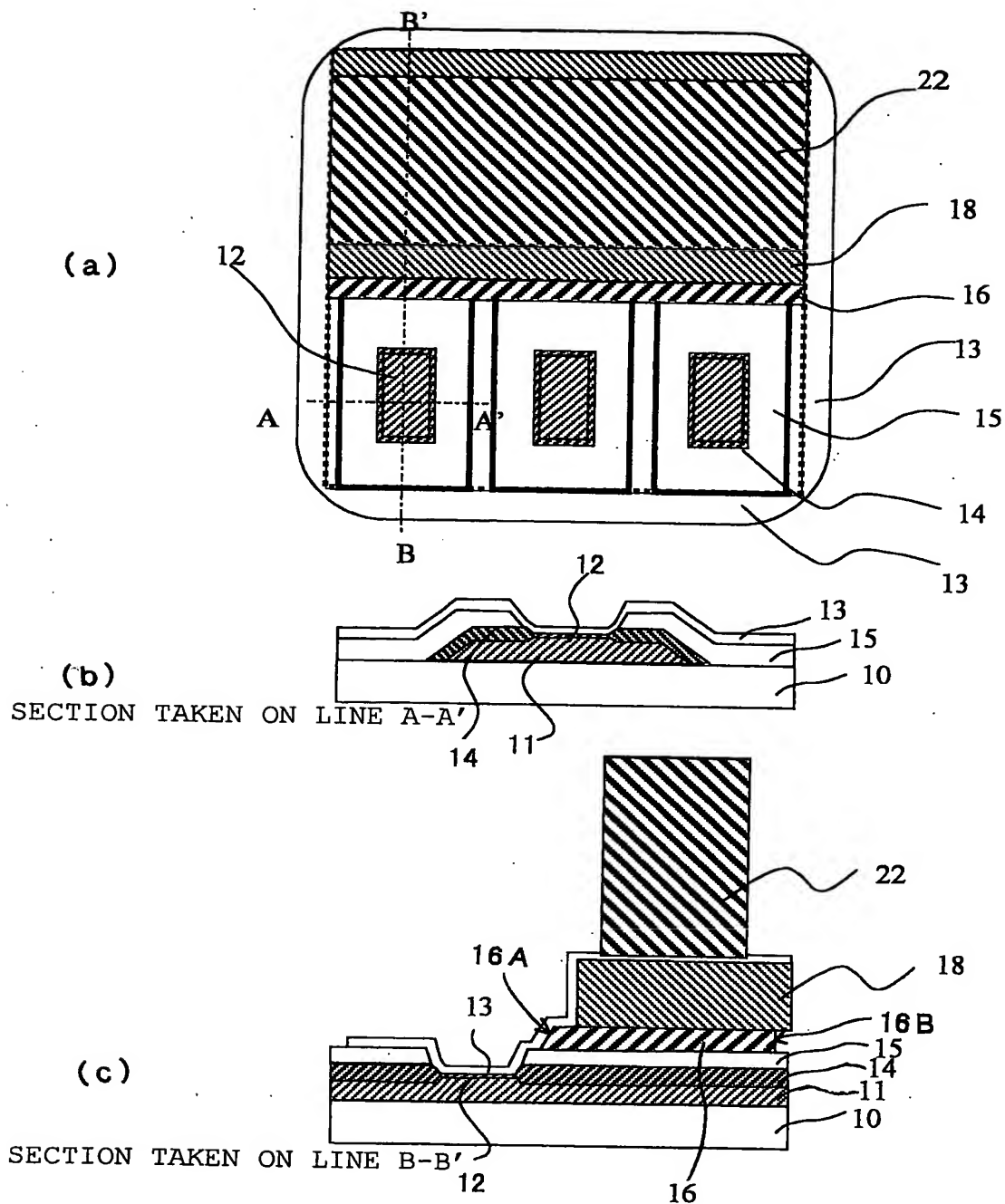
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FIG.28



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FIG.29



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FIG.30

